

II. AMENDMENTS OF THE CLAIMS

This listing of claims replaces all prior versions, or listings of claims.

1-11. (Cancelled).

12. (Previously presented) A resistor for a semiconductor device, the resistor comprising:
a silicide section positioned in a trough in one of a plurality of back-end-of-line (BEOL) layers; and
a polysilicon base positioned in the trough and below the silicide section;
wherein the silicide section has a silicidation temperature less than a damaging temperature of the plurality of BEOL layers.

13. (Original) The resistor of claim 12, wherein the silicide section includes cobalt silicide (CoSi) and has a resistivity of no less than approximately $14\ \mu$ -ohms/cm and no greater than approximately $20\ \mu$ -ohms/cm.

14. (Original) The resistor of claim 12, wherein the silicide section includes palladium silicide (PdSi) and has a resistivity of no less than approximately $25\ \mu$ -ohms/cm and no greater than approximately $30\ \mu$ -ohms/cm.

15. (Original) The resistor of claim 12, wherein the silicide section includes platinum silicide (PtSi) and has a resistivity of no less than approximately $26\ \mu$ -ohms/cm and no greater than approximately $35\ \mu$ -ohms/cm.

16. (Original) The resistor of claim 12, wherein the silicide section includes nickel silicide (NiSi) and has a resistivity of no less than approximately $14\ \mu$ -ohms/cm and no greater than approximately $20\ \mu$ -ohms/cm.
17. (Original) The resistor of claim 12, wherein the silicide section includes di-nickel silicide (Ni₂Si) and has a resistivity of no less than approximately $35\ \mu$ -ohms/cm and no greater than approximately $50\ \mu$ -ohms/cm.
18. (Original) The resistor of claim 12, wherein the silicide section includes one of molybdenum silicide (MoSi₂) and tungsten silicide (WSi₂).
19. (Cancelled).
20. (Previously presented) A semiconductor device comprising:
a silicide resistor in one of a plurality of back-end-of-line (BEOL) layers, the silicide resistor including a silicide section having a silicidation temperature less than a damaging temperature of the plurality of BEOL layers and a polysilicon base positioned below the silicide section;
wherein the silicide section and the polysilicon base are positioned in a trough in one of the plurality of back-end-of-line (BEOL) layers.